

# SKNa 102



## Stud Diode

## Avalanche Diode

### SKNa 102

#### Publish Data

#### Features

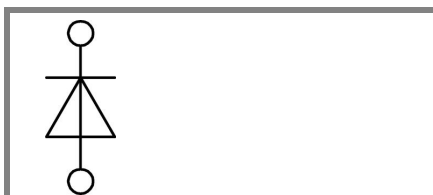
- Avalanche type reverse characteristic
- Reverse voltages up to 5000 V
- Hermetic metal case with ceramic insulator and extra long creepage distances
- Threaded stud ISO M12
- Cooling via heatsinks
- SKN: Anode to stud

#### Typical Applications

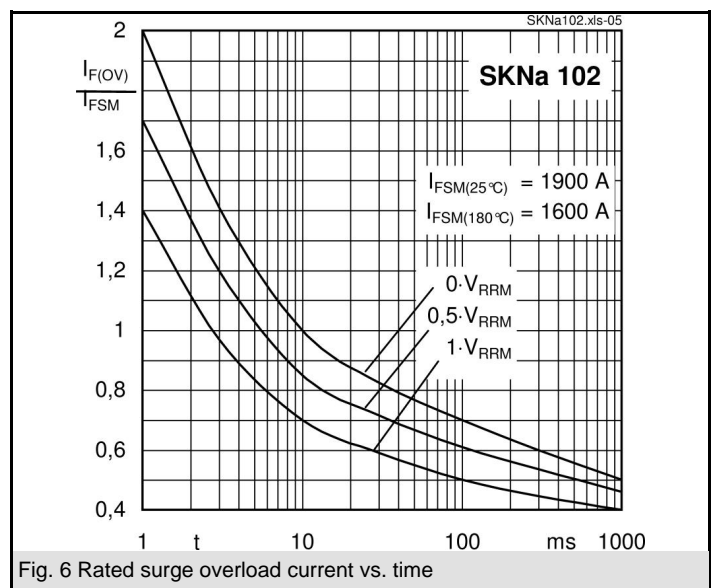
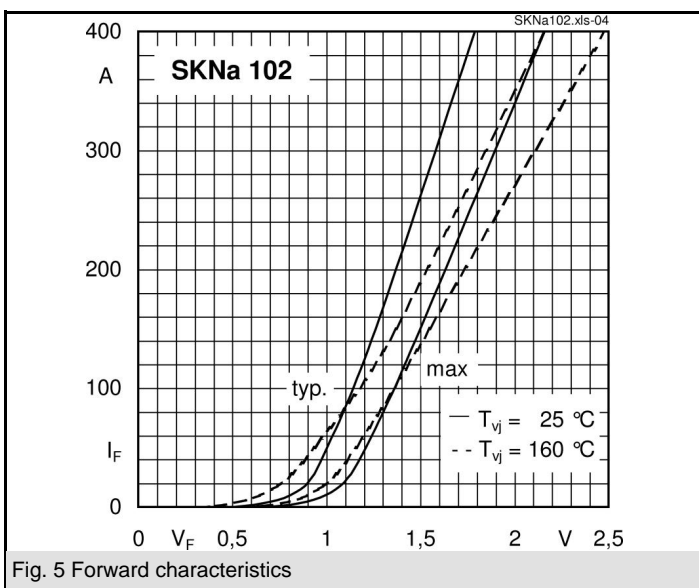
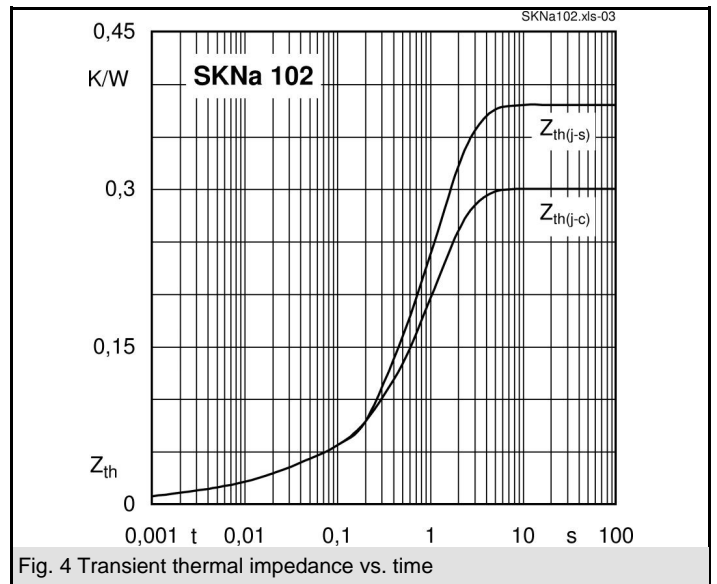
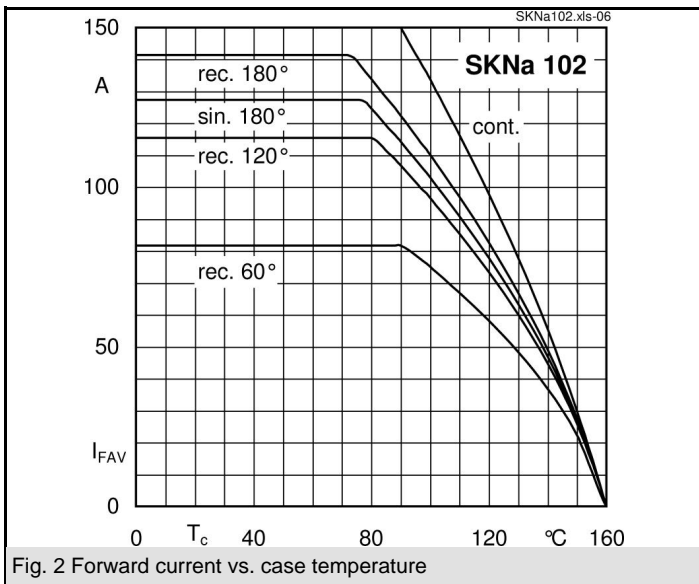
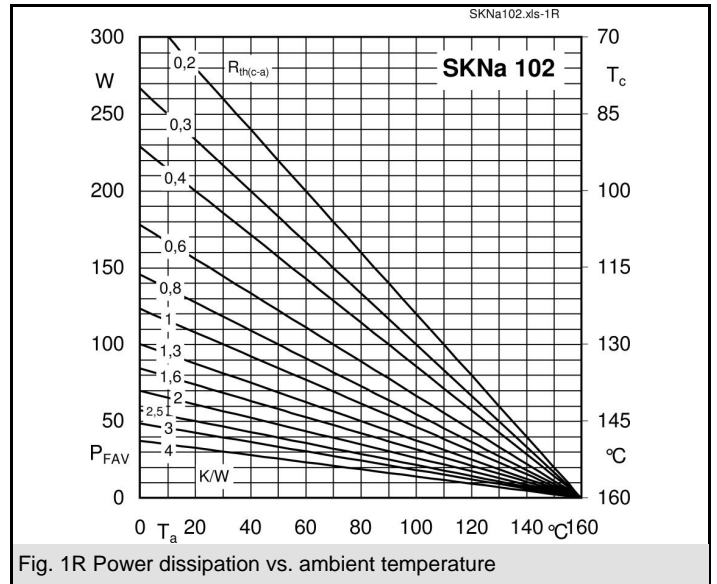
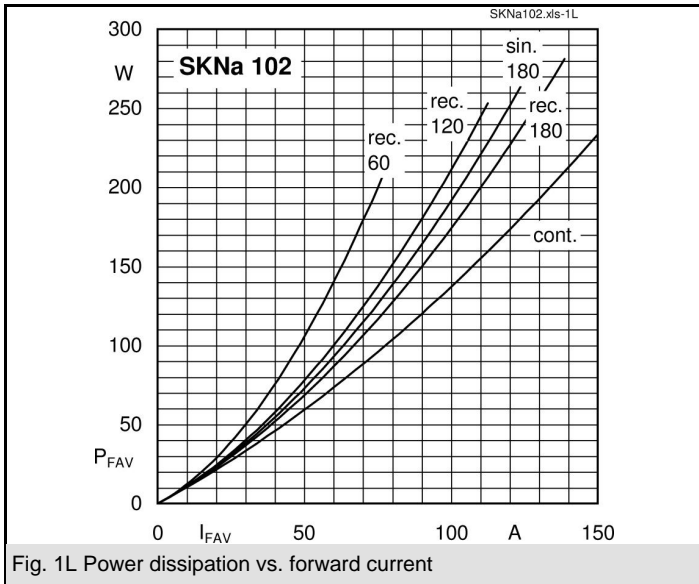
- High voltage rectifier diode for traction and heavy duty applications
- Series connections for high voltage applications
- Non-controllable and half-controllable rectifiers
- Free-wheeling diodes

| $V_{(BR)min}$<br>V | $I_{FRMS} = 200$ A<br>(maximum value for continuous operation)<br>$I_{FAV} = 125$ A (sin. 180; $T_c = 80$ °C) | $C_{max}$<br>μF | $R_{min}$<br>Ω |
|--------------------|---|-----------------|----------------|
| 3600               | SKNa 102/36   |                 |                |
| 4000               | SKNa 102/40   |                 |                |
| 4200               | SKNa 102/42   |                 |                |
| 4500               | SKNa 102/45   |                 |                |
| 4600               | SKNa 102/46   |                 |                |
| 4800               | SKNa 102/48   |                 |                |
| 5000               | SKNa 102/50   |                 |                |

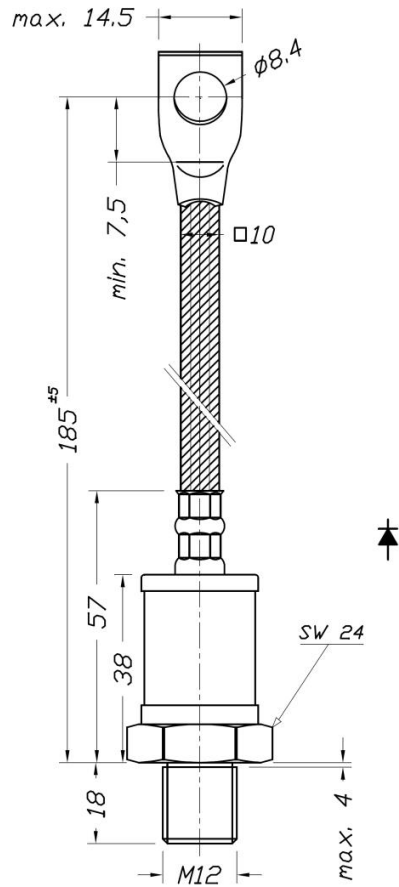
| Symbol        | Conditions                                | Values         | Units            |
|---------------|---|----------------|------------------|
| $I_{FAV}$     | sin. 180 ; $T_c = 80$ (102) °C            | 125 (100)      | A                |
| $I_D$         | K 1,1; $T_a = 45$ °C; B2 / B6             | 114 / 162      | A                |
|               | K 1,1F; $T_a = 35$ °C; B2 / B6            | 189 / 266      | A                |
| $I_{FSM}$     | $T_{vj} = 25$ °C; 10 ms                   | 1900           | A                |
|               | $T_{vj} = 160$ °C; 10 ms                  | 1600           | A                |
| $i^2t$        | $T_{vj} = 25$ °C; 8,3 ... 10 ms           | 18000          | A <sup>2</sup> s |
|               | $T_{vj} = 160$ °C; 8,3 ... 10 ms          | 12500          | A <sup>2</sup> s |
| $V_F$         | $T_{vj} = 25$ °C; $I_F = 300$ A           | max. 1,9       | V                |
| $V_{(TO)}$    | $T_{vj} = 150$ °C                         | max. 1         | V                |
| $r_T$         | $T_{vj} = 150$ °C                         | max. 3,7       | mΩ               |
| $I_{RD}$      | $T_{vj} = 25$ °C; $V_{RD} = V_{(BR)min}$  | max. 1000      | μA               |
|               | $T_{vj} = 160$ °C; $V_{RD} = V_{(BR)min}$ | max. 15        | mA               |
| $P_{RSM}$     | $T_{vj} = 160$ °C; $t_p = 10$ μs          | 36             | kW               |
| $R_{th(j-c)}$ |   | 0,3            | K/W              |
| $R_{th(c-s)}$ |   | 0,08           | K/W              |
| $T_{vj}$      |   | - 40 ... + 160 | °C               |
| $T_{stg}$     |   | - 40 ... + 160 | °C               |
| $V_{isol}$    |   | -              | V~               |
| $M_s$         | to heatsink                               | 10             | Nm               |
|               |   | 90             | lb.in.           |
| a             |   | 5 * 9,81       | m/s <sup>2</sup> |
| m             | approx.                                   | 110            | g                |
| Case          |   | E 44           |                  |



SKN



Dimensions in mm



CASE E 44 (IEC 60191: A 9 MA modified)

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